

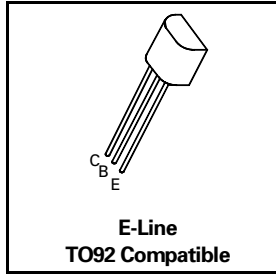
NPN SILICON PLANAR MEDIUM POWER TRANSISTORS

ZTX452
ZTX453

ISSUE 2 – MARCH 1994

FEATURES

- * 100 Volt V_{CE0}
- * 1 Amp continuous current
- * $P_{tot} = 1$ Watt



ABSOLUTE MAXIMUM RATINGS.

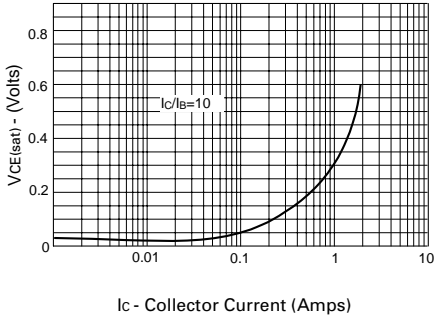
PARAMETER	SYMBOL	ZTX452	ZTX453	UNIT
Collector-Base Voltage	V_{CBO}	100	120	V
Collector-Emitter Voltage	V_{CEO}	80	100	V
Emitter-Base Voltage	V_{EBO}	5		V
Peak Pulse Current	I_{CM}	2		A
Continuous Collector Current	I_C	1		A
Power Dissipation at $T_{amb}=25^\circ\text{C}$	P_{tot}	1		W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +200		$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$).

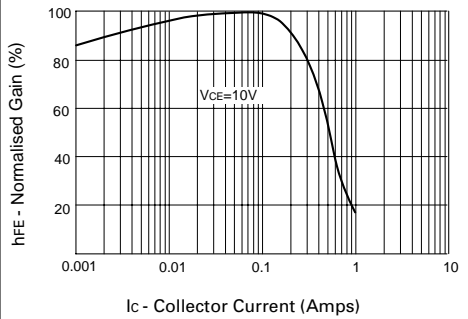
PARAMETER	SYMBOL	ZTX452		ZTX453		UNIT	CONDITIONS.
		MIN.	MAX.	MIN.	MAX.		
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	100		120		V	$I_C=100\mu\text{A}$
Collector-Emitter Sustaining Voltage	$V_{CEO(sus)}$	80		100		V	$I_C=10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	5		5		V	$I_E=100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}		0.1		0.1	μA μA	$V_{CB}=80\text{V}$ $V_{CB}=100\text{V}$
Emitter Cut-Off Current	I_{EBO}		0.1		0.1	μA	$V_{EB}=4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		0.7		0.7	V	$I_C=150\text{mA}$, $I_B=15\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		1.3		1.3	V	$I_C=150\text{mA}$, $I_B=15\text{mA}^*$
Static Forward Current Transfer Ratio	h_{FE}	40 10	150	40 10	200		$I_C=150\text{mA}$, $V_{CE}=10\text{V}^*$ $I_C=1\text{A}$, $V_{CE}=10\text{V}^*$
Transition Frequency	f_T	150		150		MHz	$I_C=50\text{mA}$, $V_{CE}=10\text{V}$ $f=100\text{MHz}$
Output Capacitance	C_{obo}		15		15	pF	$V_{CB}=10\text{V}$, $f=1\text{MHz}$

ZTX452 ZTX453

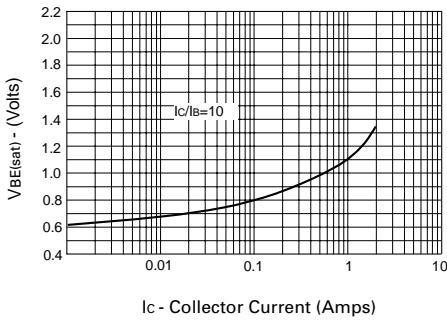
TYPICAL CHARACTERISTICS



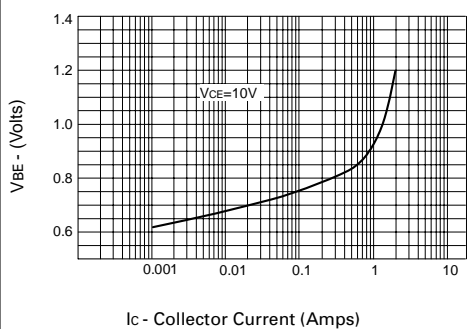
$V_{CE(sat)}$ v I_C



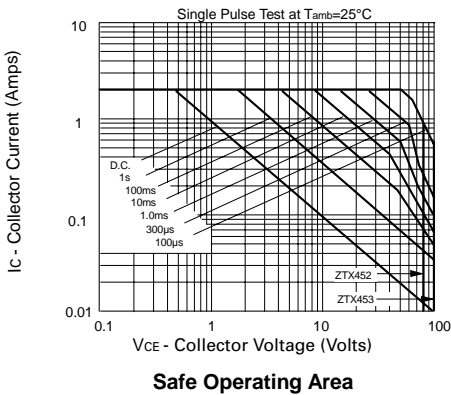
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area